

KSC2073

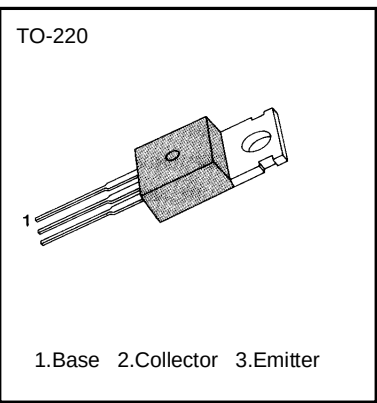
NPN EPITAXIAL SILICON TRANSISTOR

TV VERTICAL DEFLECTION OUTPUT

- Complement to KSA940
- Collector-Base Voltage $V_{CBO} = 150V$

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	150	V
Collector-Emitter Voltage	V_{CEO}	150	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1.5	A
Collector Dissipation ($T_C=25^{\circ}C$)	P_C	25	W
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 ~ 150	$^{\circ}C$

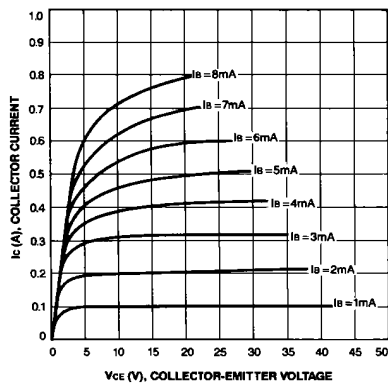


ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$)

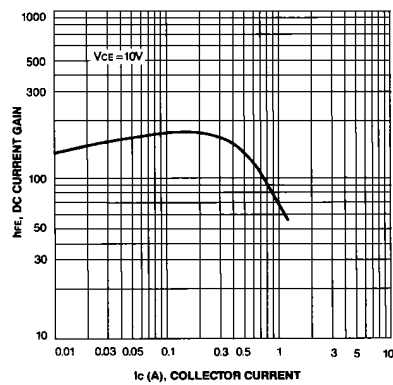
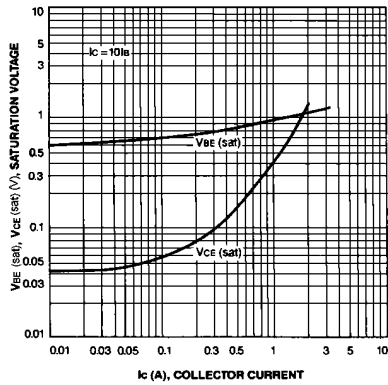
Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = 500\mu A, I_E = 0$	150			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = 10mA, I_B = 0$	150			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -500\mu A, I_C = 0$	5			V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 120V, I_E = 0$			10	μA
DC Current Gain	h_{FE}	$V_{CE} = 10V, I_C = 0.5A$	40	75	140	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500mA, I_B = 50mA$			1	V
Current Gain Bandwidth Product	f_T	$V_{CE} = 10V, I_E = 0.5A$		4		MHz
Output Capacitance	C_{OB}	$V_{CB} = 10V, I_E = 0$ $f = 1MHz$		50		pF



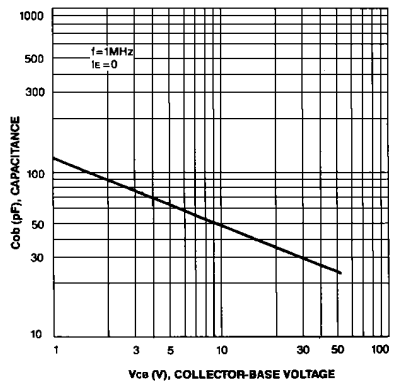
STATIC CHARACTERISTIC



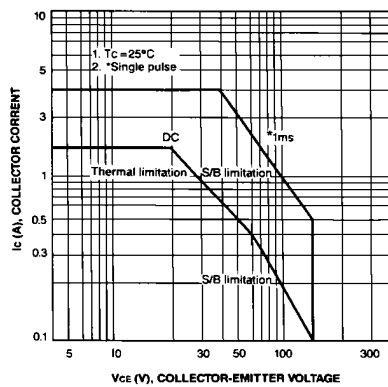
DC CURRENT GAIN

BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE

COLLECTOR OUTPUT CAPACITANCE



SAFE OPERATING AREA



POWER DERATING

